

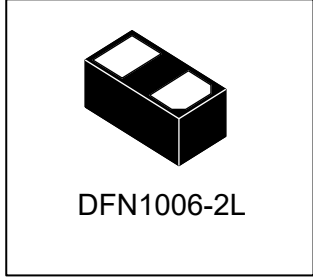
RB751BS-40

S-RB751BS-40

Schottky barrier diode

1. FEATURES

- Extremely small surface mounting type.
- Ultra low VF
- High reliability.
- We declare that the material of product compliance with RoHS requirements.
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.



2. APPLICATIONS

- Low current rectification
- Silicon epitaxial planar



3. DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
RB751BS-40	5	10000/Tape&Reel

4. MAXIMUM RATINGS(Ta = 25°C)

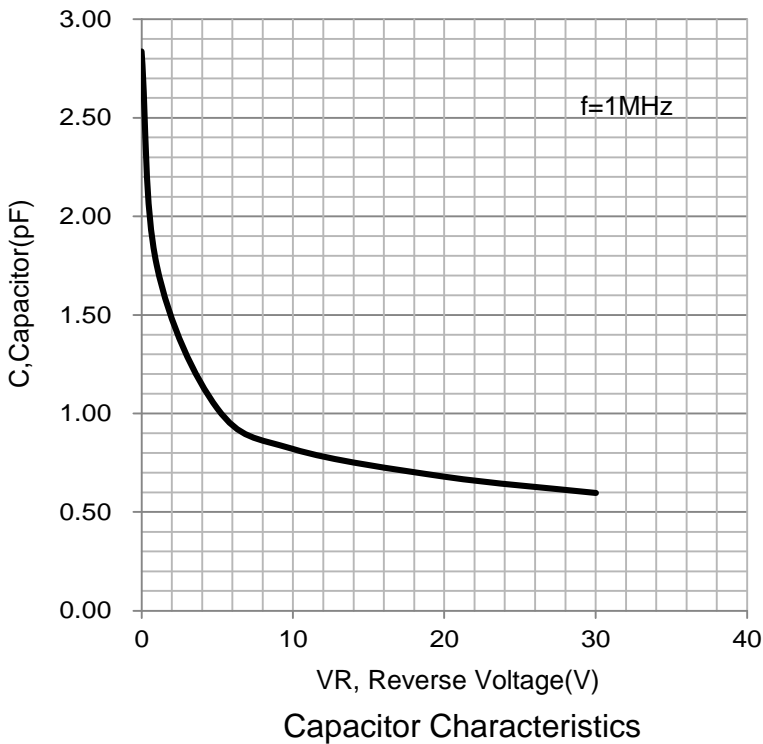
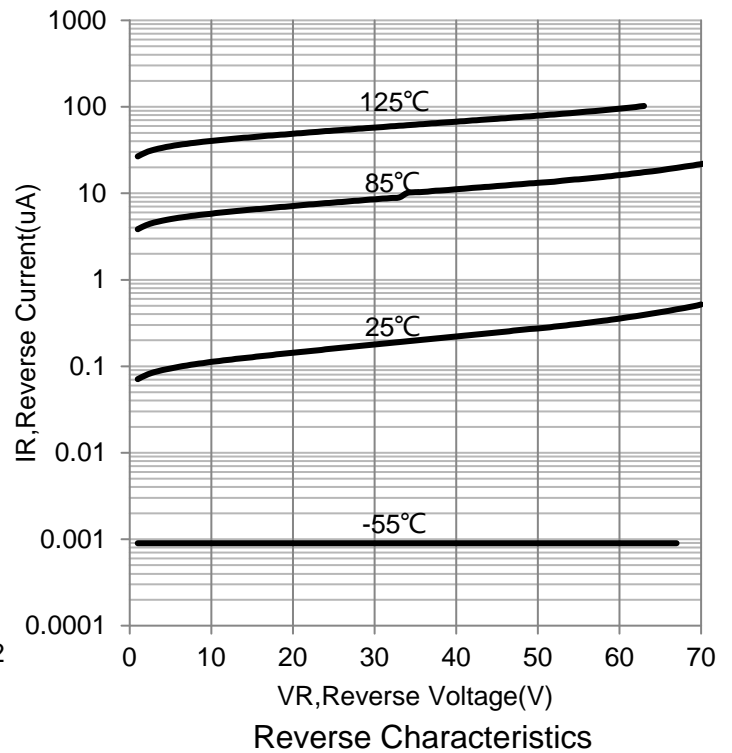
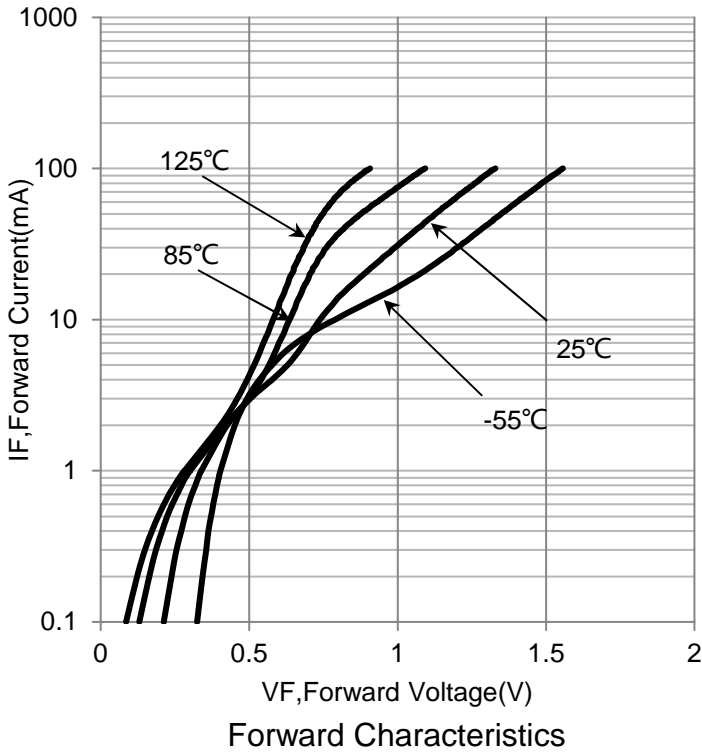
Parameter	Symbol	Limits	Unit
Reverse voltage (repetitive peak)	VRM	40	V
Reverse voltage (DC)	VR	30	V
Average Rectified Forward Current	IO	30	mA
Peak Forward Surge Current (60Hz · 1cyc)	IFSM	200	mA
Junction Temperature	Tj	125	°C
Storage Temperature	TSTG	-40~+125	°C

5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

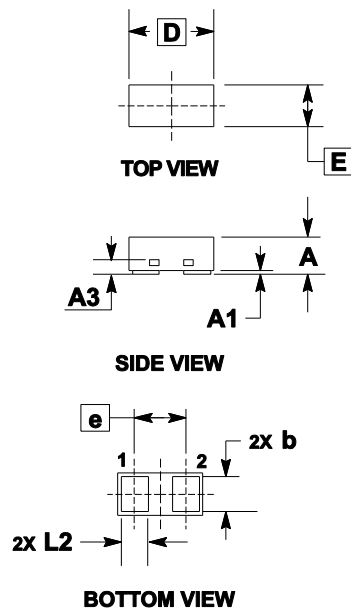
Parameter	Symbol	Min.	Typ.	Max.	Unit
Forward voltage (IF =1mA)	VF	-	-	0.37	V
Reverse current (VR=30V)	IR	-	-	0.5	µA
Capacitance between terminals (VR=1V,f=1MHz)	Ct	-	2	-	pF



6. ELECTRICAL CHARACTERISTICS CURVES



7. OUTLINE AND DIMENSIONS

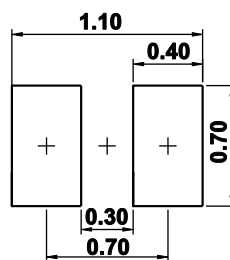


Notes:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.43	0.48	0.53	0.017	0.019	0.021
A1	0.00	---	0.05	0.000	---	0.002
A3	0.127REF			0.005REF		
b	0.44	0.49	0.54	0.017	0.019	0.021
D	0.95	1	1.05	0.037	0.039	0.041
e	0.64REF			0.025REF		
E	0.50	0.6	0.65	0.020	0.024	0.026
L2	0.20	0.25	0.3	0.008	0.010	0.012

8. SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

